Micro Commercial Components
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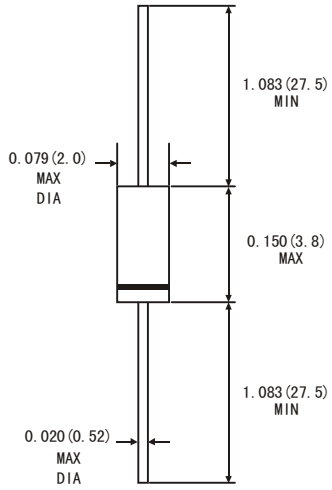
BAT86

SMALL SIGNAL SCHOTTKY DIODES

Features

- For general purpose applications
- These diodes features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage,such as electrostatic discharges.
- These diode is also available in the Mini-MELF case with type designation LL86
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices,and low logic applications.

DO-35



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: Do-35 glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Repetitive Peak Reverse Voltage	V_R	50	V
Forward Continuous Current at T =25^{0}C	I_F	200[1)]	mA
Repetitive Peak Forward Current at t<1s,ä< 0.5,T_A=25^{0}C	I_{FRM}	300[1)]	mA
Power Dissipation at T_A=65^{0}C	Ptot	200[1)]	mW
Junction temperature	T_J	125	^{0}C
Ambient Operating temperature Range	T_A	-55~+125	^{0}C
Storage Temperature Range	T_{STG}	-55~+150	^{0}C
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature			

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakdown voltage Tested with 10μA pulses	$V_{(BR)R}$	50			V
Forward voltage Pulse Test t_p <300μs,δ <2% at I_F=0.1mA, at I_F=1mA, at I_F=10mA, at I_F=30mA, at I_F=100mA	 V_F V_F V_F V_F V_F		 0.200 0.272 0.365 0.460 0.700	 0.300 0.380 0.450 0.600 0.900	 V V V V V
Leakage current V_R=25V	I_R		0.2	0.5	μA
Junction Capacitance at V_R=1V ,f=1MHz	C_J			8	pF
Reverse recovery time Form I_F=10mA,I_R=10mA,I_R=1mA	trr			5	ns
Thermal resistance junction to ambient Air	$R_{\theta JA}$			300 [1)]	K/W
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature(DO-35)					